

PHP18NQ11T

N-channel TrenchMOS standard level FET Rev. 02 — 10 March 2010

Product data sheet

Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- Class-D audio amplifiers
- DC-to-DC convertors

- Inverters
- Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	110	V
I_D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see <u>Figure 1</u> and <u>3</u>	-	-	18	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	79	W
Dynamic	Dynamic characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 18 \text{ A};$ $V_{DS} = 80 \text{ V}; T_j = 25 \text{ °C};$ see Figure 11	-	8	-	nC
Static ch	naracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A};$ $T_j = 25 ^{\circ}\text{C};$ see Figure 9 and 10	-	80	90	mΩ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	D
3	S	source		$G \longrightarrow A$
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHP18NQ11T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	110	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	110	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	13	Α
		$V_{GS} = 10 \text{ V}$; $T_{mb} = 25 \text{ °C}$; see <u>Figure 1</u> and <u>3</u>	-	18	Α
I_{DM}	peak drain current	$t_p \le 10 \mu\text{s}; \text{ pulsed}; T_{mb} = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 3}}{}$	-	72	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	79	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	18	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	72	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 11 \text{ A; } V_{sup} \leq 25 \text{ V;}$ unclamped; $t_p = 0.1 \text{ ms; } R_{GS} = 50 \Omega$	-	70	mJ

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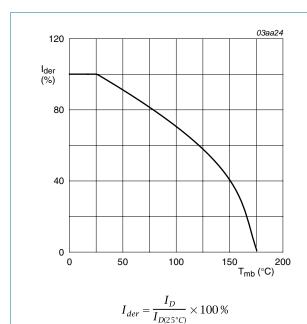


Fig 1. Normalized continuous drain current as a function of mounting base temperature

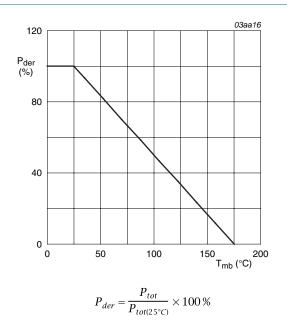


Fig 2. Normalized total power dissipation as a function of mounting base temperature

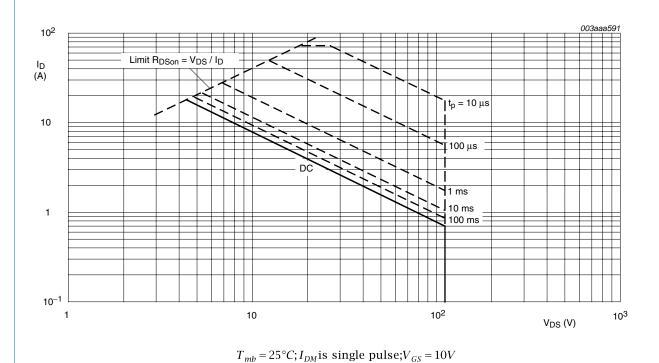
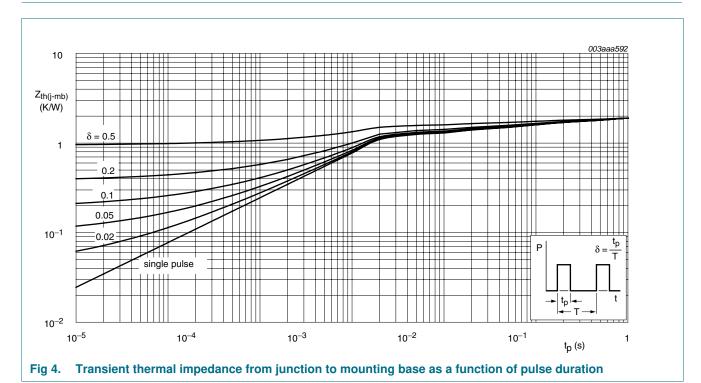


Fig 3. Safe operating area: continuous and peak currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



PHP18NQ11T_2

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 ^{\circ}C$	98	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 8</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 8	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 8	-	-	4.4	V
I _{DSS}	drain leakage current	$V_{DS} = 110 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 110 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS} g	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
Doon	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 175 °C;$ see Figure 9 and 10	-	-	243	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 9 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 9 and 10	-	80	90	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 18 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	21	-	nC
Q _{GS}	gate-source charge	$T_j = 25 ^{\circ}\text{C}$; see Figure 11	-	4	-	nC
Q_{GD}	gate-drain charge		-	8	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	633	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	103	-	pF
C _{rss}	reverse transfer capacitance		-	61	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2.7 \Omega; V_{GS} = 10 \text{ V};$	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 \text{ °C}; I_D = 18.5 A$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	18	-	ns
t _f	fall time		-	12	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 18 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 13	-	0.92	1.2	V
t _{rr}	reverse recovery time	$I_S = 18 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	55	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	135	-	nC

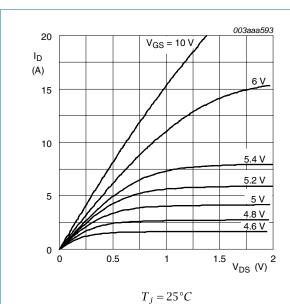
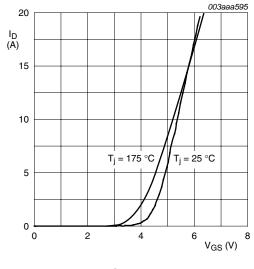
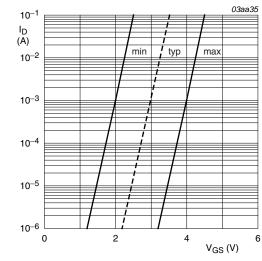


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



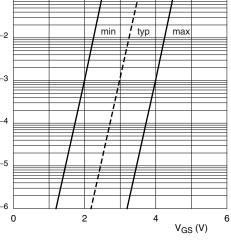
 $T_i = 25$ °C and 175°C; $V_{DS} > I_D \times R_{DSon}$

Transfer characteristics: drain current as a Fig 6. function of gate-source voltage; typical values

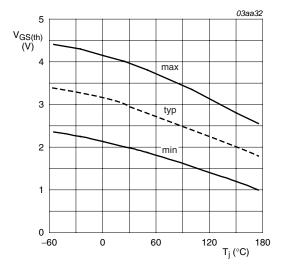


 $T_i = 25 \,^{\circ}C; V_{DS} = 5V$ Sub-threshold drain current as a function of Fig 7.

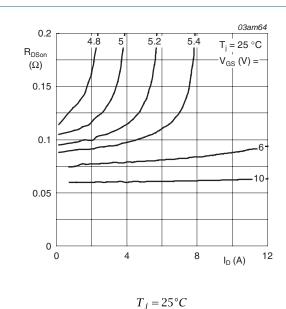
gate-source voltage



Gate-source threshold voltage as a function of Fig 8. junction temperature



 $I_D = 1 \, mA; V_{DS} = V_{GS}$



 $T_j = 23$ C

Fig 9. Drain-source on-state resistance as a function of drain current; typical values

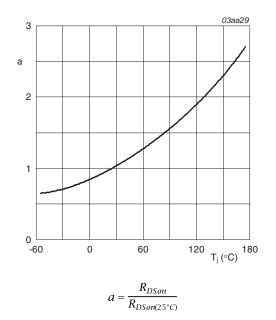
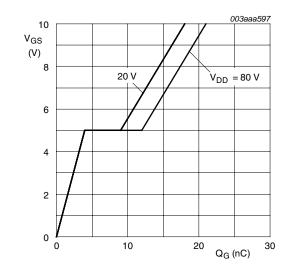
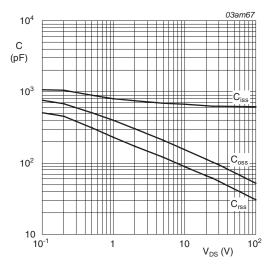


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature



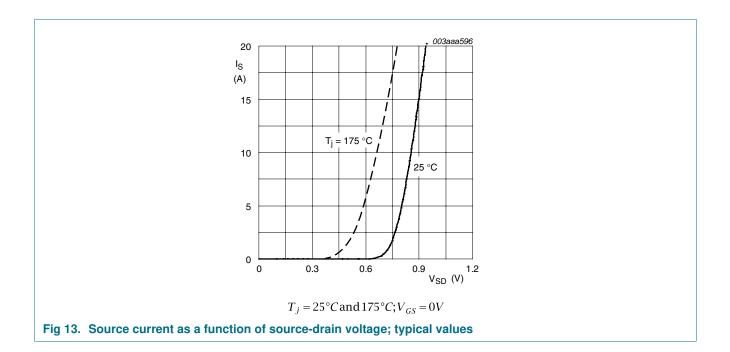
 $I_D = 3A; V_{DD} = 20V \text{ and } 80V$

Fig 11. Gate-source voltage as a function of gate charge; typical values

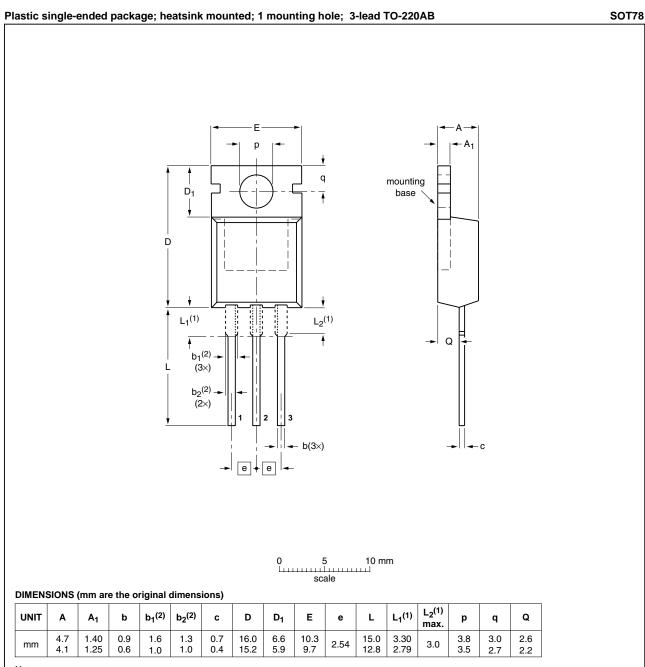


$$V_{GS} = 0V; f = 1MHz$$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline



Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	TA PROJECTION		ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

Fig 14. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP18NQ11T_2	20100310	Product data sheet	-	PHP18NQ11T-01
guidelin		of this data sheet has bee of NXP Semiconductors. have been adapted to the		·
PHP18NQ11T-01 (9397 750 12305)	20031113	Product data	-	-

Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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PHP18NQ11T 2

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PHP18NQ11T

N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline9
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information12